

TOSHIBA Transistor Silicon NPN Epitaxial Type

TPCP8701

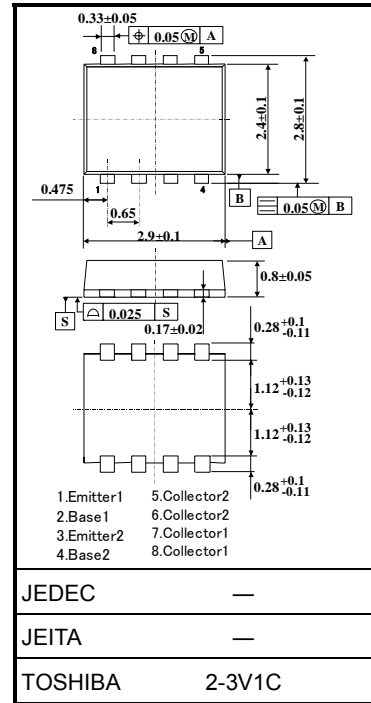
Portable Equipment Applications

Switching Applications

Inverter Lighting Applications

- Small footprint due to small and thin package
- High DC current gain : $h_{FE} = 400$ to 1000 ($I_C = 0.3$ A)
- Low collector-emitter saturation : $V_{CE(sat)} = 0.14$ V (max)
- High-speed switching : $t_f = 120$ ns (typ.)

Unit: mm



Weight: 0.017 g (typ.)

Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit
Collector-base voltage		V_{CBO}	100	V
Collector-emitter voltage		V_{CEX}	80	V
		V_{CEO}	50	V
Emitter-base voltage		V_{EBO}	7	V
Collector current	DC (Note 1)	I_C	3.0	A
	Pulse (Note 1)	I_{CP}	5.0	
Base current		I_B	300	mA
Collector power dissipation (t = 10s)	Single-device operation	P_C (Note 2)	1.77	W
	Single-device value at dual operation		0.95	
Collector power dissipation (DC)	Single-device operation	P_C (Note 2)	0.94	W
	Single-device value at dual operation		0.54	
Junction temperature		T_j	150	°C
Storage temperature range		T_{stg}	-55 to 150	°C

Note 1: Please use devices on condition that the junction temperature is below 150°C.

Note 2: Mounted on FR4 board (glass epoxy, 1.6 mm thick, Cu area: 645 mm²)

Note 3: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings.

Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Figure 1. Circuit configuration (top view)

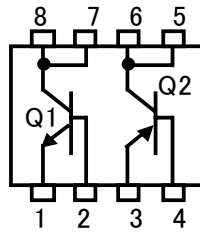
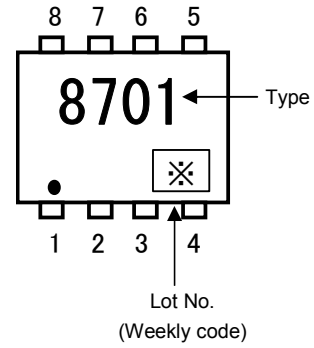
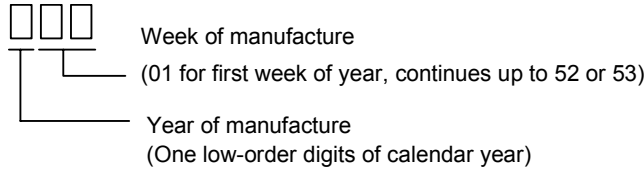


Figure 2. Marking (Note 4)



Note 4: ● on lower left on the marking indicates Pin 1.

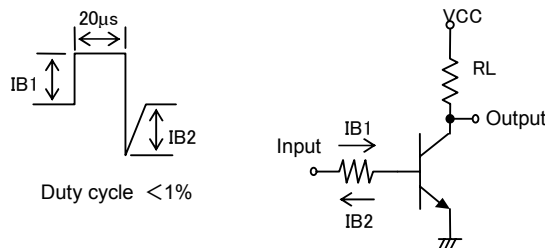
※ Weekly code: (Three digits)

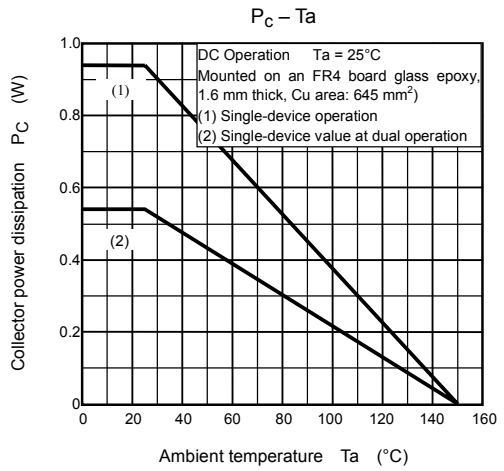
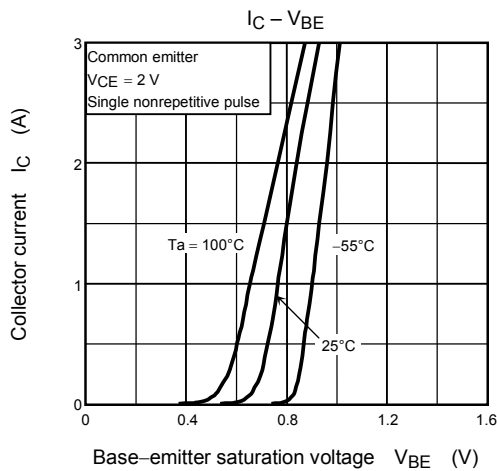
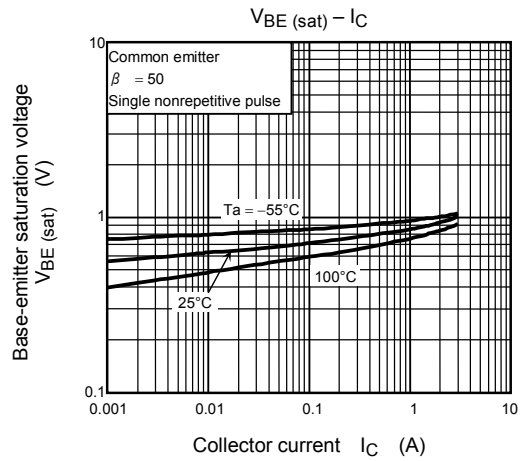
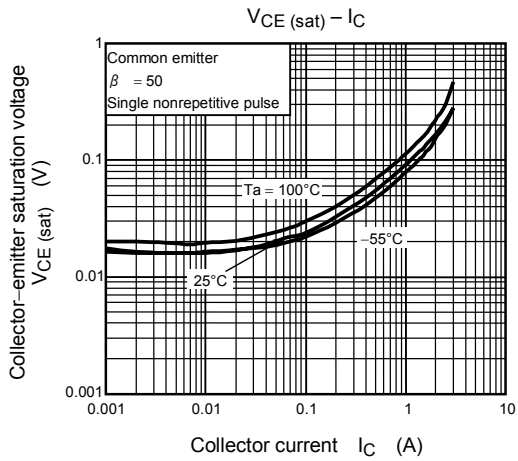
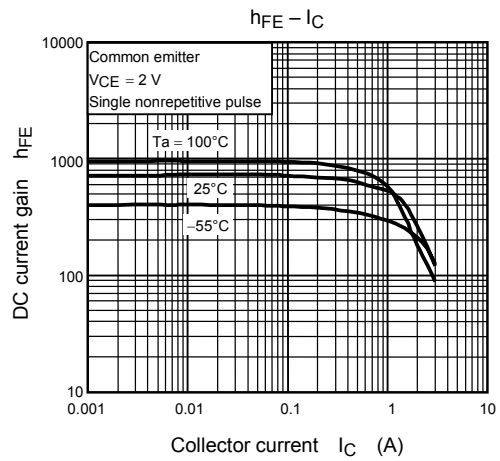
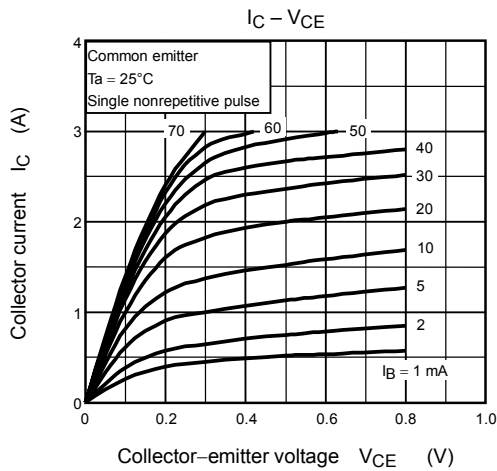


Electrical Characteristics (Ta = 25°C)

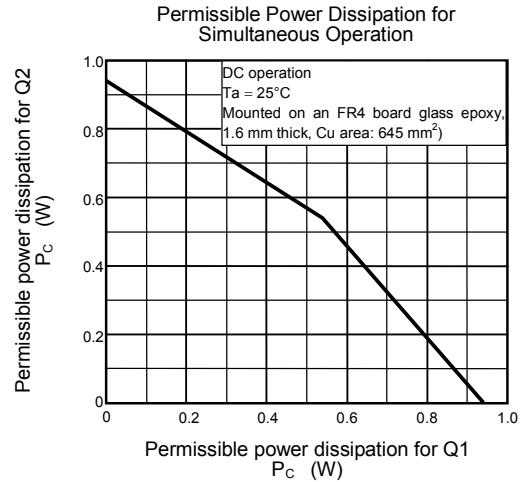
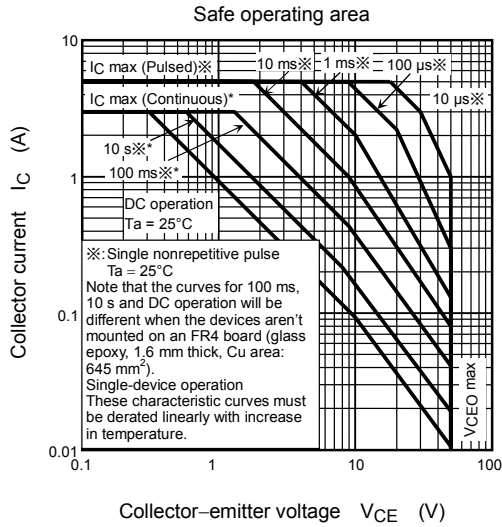
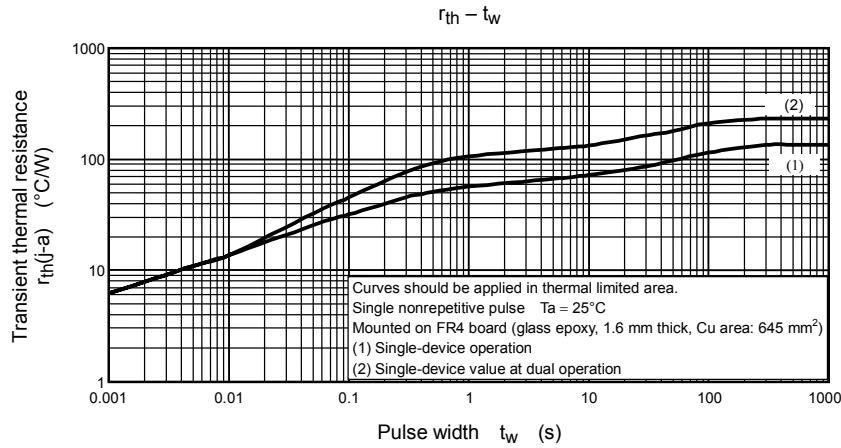
Characteristics	Symbol	Test Condition	Min	Typ.	Max	Unit
Collector cut-off current	I_{CBO}	$V_{CB} = 100\text{ V}, I_E = 0$	—	—	100	nA
Emitter cut-off current	I_{EBO}	$V_{EB} = 7\text{ V}, I_C = 0$	—	—	100	nA
Collector-emitter brakedown voltage	$V_{(BR)CEO}$	$I_C = 10\text{ mA}, I_B = 0$	50	—	—	V
DC current gain	$h_{FE} (1)$	$V_{CE} = 2\text{ V}, I_C = 0.3\text{ A}$	400	—	1000	
	$h_{FE} (2)$	$V_{CE} = 2\text{ V}, I_C = 1\text{ A}$	200	—	—	
Collector-emitter saturation voltage	$V_{CE(sat)}$	$I_C = 1\text{ A}, I_B = 20\text{ mA}$	—	—	0.14	V
Base-emitter saturation voltage	$V_{BE(sat)}$	$I_C = 1\text{ A}, I_B = 20\text{ mA}$	—	—	1.10	V
Collector output capacitance	C_{ob}	$V_{CB} = 10\text{ V}, I_E = 0, f = 1\text{ MHz}$	—	13	—	pF
Switching time	Rise time	See Figure 3 circuit diagram $V_{CC} \approx 30\text{ V}, R_L = 30\ \Omega$ $I_{B1} = -I_{B2} = 33.3\text{ mA}$	—	40	—	ns
	Storage time		—	500	—	
	Fall time		—	120	—	

Figure 3. Switching Time Test Circuit & Timing Chart





(2)



Collector power dissipation at the single-device operation is 0.94W.
 Collector power dissipation at the single-device value at dual operation is 0.54W.
 Collector power dissipation at the dual operation is set to 1.08W.

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